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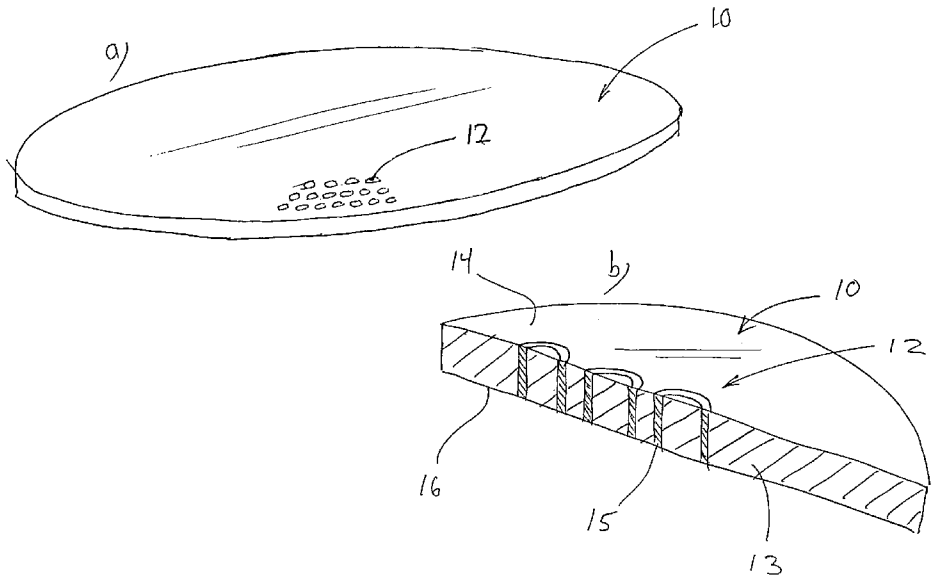
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(54) Title: ELECTRICAL CONNECTIONS IN SUBSTRATES



(57) Abstract: The invention relates to a method of making an electrical connection between a first (top) and a second (bottom) surface of a conducting or semi-conducting substrate. It comprising creating a trench in the first surface, and establishing an insulating enclosure entirely separating a portion of said substrate, defined by said trench. It also relates to a product usable as a starting substrate for the manufacture of micro-electronic and/or micro-mechanic devices, comprising a flat substrate of a semi-conducting or conducting material, and having a first and a second surface and at least one electrically conducting member extending through said substrate. The electrically conducting member is insulated from surrounding material of the flat substrate by a finite layer of an insulating material, and comprises the same material as the substrate, i.e. it is made from the wafer material.

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